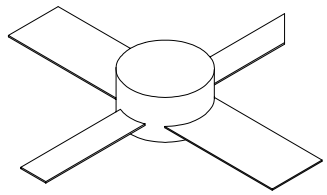
1150MP

150 Watts, 50 Volts, Class C
Avionics 1025 - 1150 MHz

GENERAL DESCRIPTION

The 1150MP is a COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1025-1150 MHz. The device has gold thin-film metallization for proven highest MTTF. The transistor includes input prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

CASE OUTLINE
55FW-1



ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C[2]	250 Watts Peak
Maximum Voltage and Current	
BVces Collector to Emitter Voltage	60 Volts
BVebo Emitter to Base Voltage	4.0 Volts
Ic Collector Current	6.0 Amps Peak
Maximum Temperatures	
Storage Temperature	- 65 to +150 °C
Operating Junction Temperature	+ 200 °C

ELECTRICAL CHARACTERISTICS @ 25°C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P_{OUT}	Power Out	F= 1025-1150 MHz	140	150		W
P_{IN}	Power Input	Vcc = 50 Volts			30	W
P_G	Power Gain	PW = 10 μsec, DF = 1%	7.0	7.5		dB
ηc	Efficiency		35	38		%
VSWR	Load Mismatch Tolerance	F = 1090 MHz			10:1	

FUNCTIONAL CHARACTERISTICS @ 25°C

BVebo	Emitter to Base Breakdown	Ie = 1 mA	3.5			V
BVces	Collector to Emitter Breakdown	Ic = 10mA	65			V
Hfe	DC Current Gain	Vce = 5V, Ic = 500 mA	15		120	
Cob	Output Capacitance	Vcb = 50 V, f = 1 MHz			16	pF
θjc[2]	Thermal Resistance	Tc=25°C			0.6	°C/W

Note 1: At rated output power and pulse conditions
2: At rated pulse conditions

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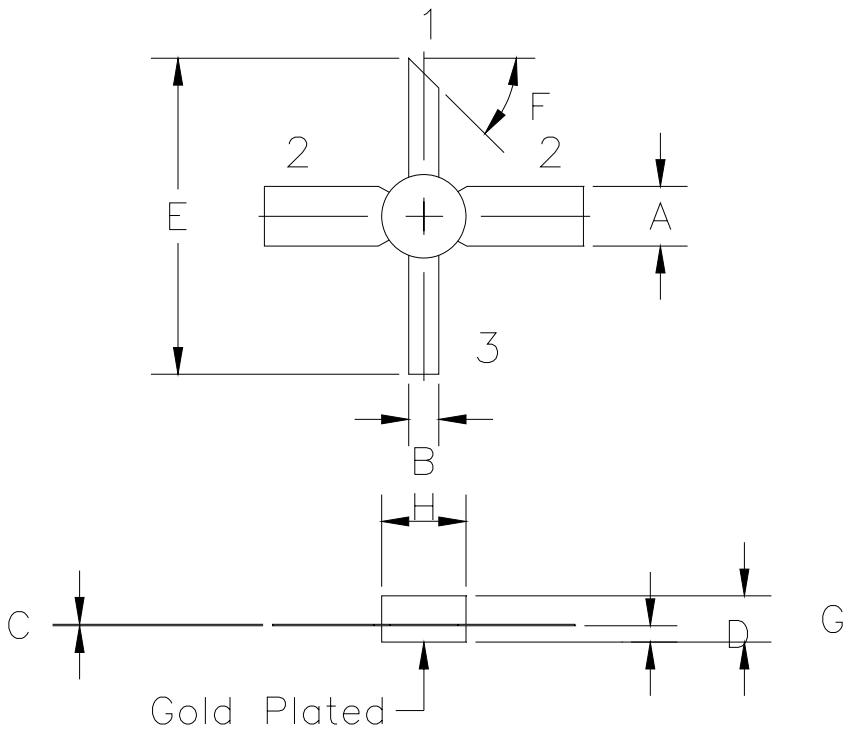
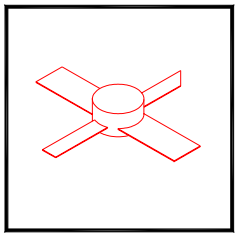


DIM	MILLIMETER	±TOL	INCHES	±TOL
A	5.08	.13	.200	.005
B	7.11 DIA	.13	.280 DIA	.005
C	0.13	.02	.005	.001
D	1.40	.13	.055	.005
E	26.92	.64	1.060	.025
F	45°	5°	45°	5°
G	3.94	REF	.155	REF
H	2.54	.13	.100	.005

STYLE 1:
PIN1 = COLLECTOR
2 = BASE (2X)
3 = EMITTER

STYLE 2:
PIN1 = COLLECTOR
2 = EMITTER (2X)
3 = BASE



GHz TECHNOLOGY
RF – MICROWAVE SILICON POWER TRANSISTORS

DWG NO. 55FW